

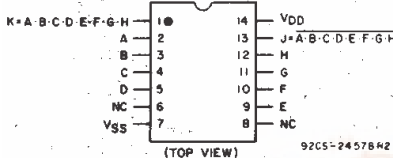


Data sheet acquired from Harris Semiconductor
SCHS053

CMOS 8-Input NAND/AND Gate

High-Voltage Types (20-Volt Rating)

■ CD4068B NAND/AND gate provides the system designer with direct implementation of the positive-logic 8-input NAND and AND functions and supplements the existing family of CMOS gates. The CD4068B types are supplied in 14-lead dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).



NC = NO CONNECTION

TERMINAL ASSIGNMENT

Features:

- Medium-Speed Operation: $t_{PHL}, t_{PLH} = 75 \text{ ns (typ.)}$ at $V_{DD} = 10 \text{ V}$
- Buffered inputs and outputs
- 5-V, 10-V, and 15-V parametric ratings
- Standardized symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of $1 \mu\text{A}$ at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package-temperature range): 1 V at $V_{DD} = 5 \text{ V}$
 2 V at $V_{DD} = 10 \text{ V}$ 2.5 V at $V_{DD} = 15 \text{ V}$
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	Min.	Max.	Units
Supply-Voltage Range (For $T_A = \text{Full Package Temperature Range}$)	3	18	V

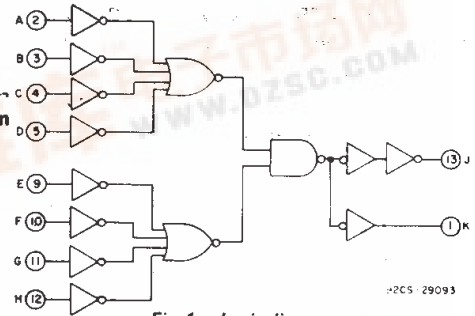
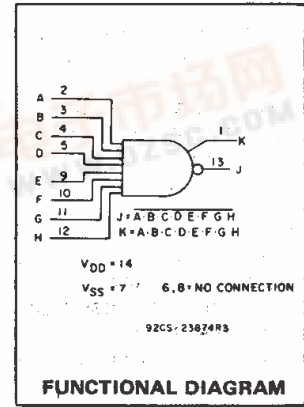


Fig. 1 - Logic diagram.

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES ($^\circ\text{C}$)							UNITS
	V_O (V)	V_{IN} (V)	V_{DD} (V)	+25							
				-55	-40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, $I_{DD} \text{ Max.}$	-	0.5	5	0.25	0.25	7.5	7.5	-	0.01	0.25	μA
	-	0.10	10	0.5	0.5	15	15	-	0.01	0.5	
	-	0.15	15	1	1	30	30	-	0.01	1	
	-	0.20	20	5	5	150	150	-	0.02	5	
Output Low (Sink) Current $I_{OL} \text{ Min.}$	0.4	0.5	5	0.64	0.61	0.42	0.36	0.51	1	-	mA
	0.5	0.10	10	1.6	1.5	1.1	0.9	1.3	2.6	-	
	1.5	0.15	15	4.2	4	2.8	2.4	3.4	6.8	-	
Output High (Source) Current, $I_{OH} \text{ Min.}$	4.6	0.5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	-	mA
	2.5	0.5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-	
	9.5	0.10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-	
	13.5	0.15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-	
Output Voltage: Low-Level, $V_{OL} \text{ Max.}$	-	0.5	5	0.05			-			0	V
	-	0.10	10	0.05			-			0	
	-	0.15	15	0.05			-			0	
Output Voltage: High-Level, $V_{OH} \text{ Min.}$	-	0.5	5	4.95			4.95			5	V
	-	0.10	10	9.95			9.95			10	
	-	0.15	15	14.95			14.95			15	
Input Low Voltage, $V_{IL} \text{ Max.}$	0.5, 4.5	-	5	1.5			-			1.5	V
	1.9	-	10	3			-			3	
	1.5, 13.5	-	15	4			-			4	
Input High Voltage, $V_{IH} \text{ Min.}$	0.5, 4.5	-	5	3.5			3.5			-	V
	1.9	-	10	7			7			-	
	1.5, 13.5	-	15	11			11			-	
Input Current $I_{IN} \text{ Max.}$	-	0.18	18	± 0.1	± 0.1	± 1	± 1	-	$\pm 10^{-5}$	± 0.1	μA

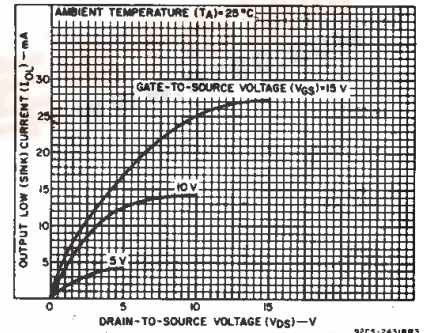


Fig. 2 - Typical output low (sink) current characteristics.

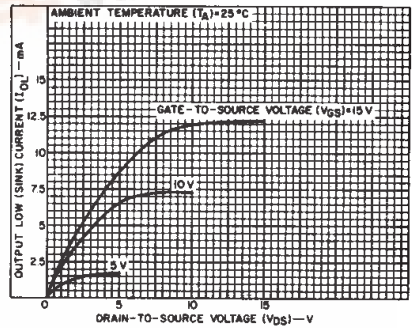
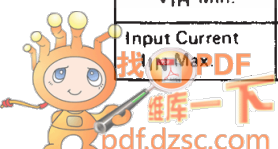


Fig. 3 - Minimum output low (sink) current characteristics.

3
COMMERCIAL CMOS
HIGH VOLTAGE ICs



CD4068B Types

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD}) Voltages referenced to V_{SS} Terminal	-0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5V to V_{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT	$\pm 10\text{mA}$
POWER DISSIPATION PER PACKAGE (P_D):	
For $T_A = -55^\circ\text{C}$ to $+100^\circ\text{C}$	500mW
For $T_A = +100^\circ\text{C}$ to $+125^\circ\text{C}$	Derate Linearly at $12\text{mW}/^\circ\text{C}$ to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE (All Package Types)}$	100mW
OPERATING-TEMPERATURE RANGE (T_A)	-55°C to $+125^\circ\text{C}$
STORAGE TEMPERATURE RANGE (T_{stg})	-65°C to $+150^\circ\text{C}$
LEAD TEMPERATURE (DURING SOLDERING):	
At distance $1/16 \pm 1/32$ inch ($1.59 \pm 0.79\text{mm}$) from case for 10s max	$+265^\circ\text{C}$

DYNAMIC ELECTRICAL CHARACTERISTICS

At $T_A = 25^\circ\text{C}$; Input $t_r, t_f = 20\text{ns}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$

CHARACTERISTIC	TEST CONDITIONS	LIMITS		UNITS	
		V_{DD} VOLTS	TYP.		MAX.
Propagation Delay Time, t_{PHL}, t_{PLH}		5	150	300	ns
		10	75	150	
		15	55	110	
Transition Time, t_{THL}, t_{TLH}		5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance, C_{IN}	Any Input	5	7.5	pF	

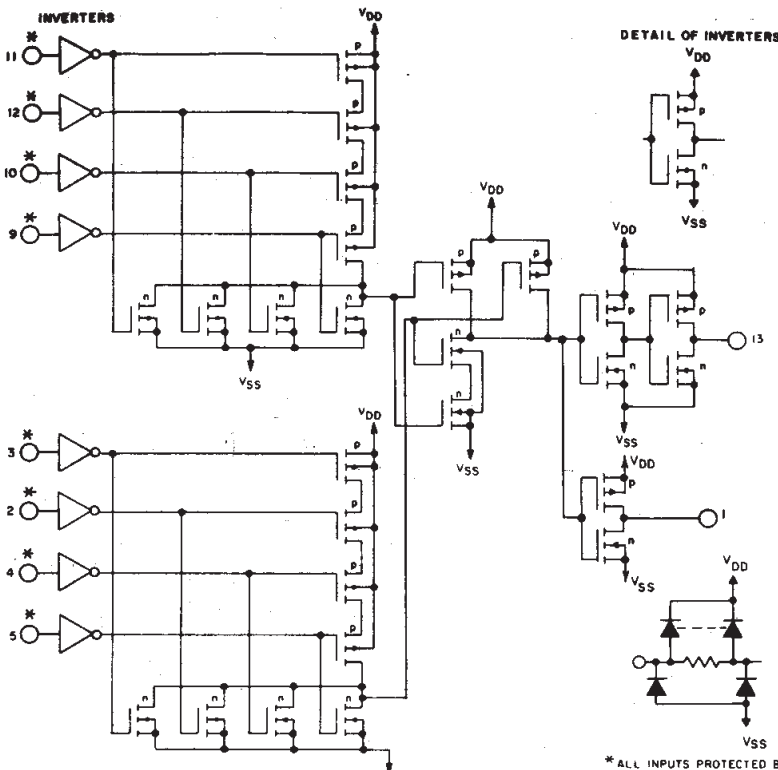


Fig. 7 - Schematic diagram.

* ALL INPUTS PROTECTED BY CMOS PROTECTION NETWORK 92CM-29094

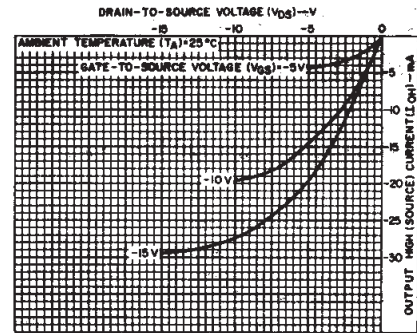


Fig. 4 - Typical output high (source) current characteristics.

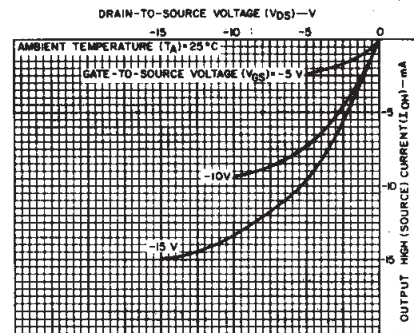


Fig. 5 - Minimum output high (source) current characteristics.

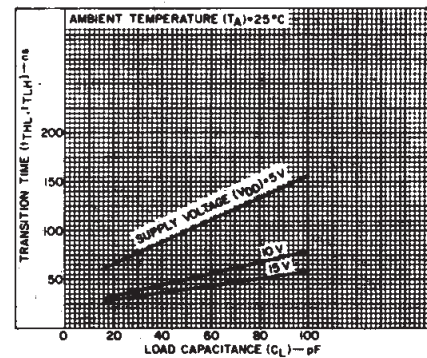


Fig. 6 - Typical transition time as a function of load capacitance.

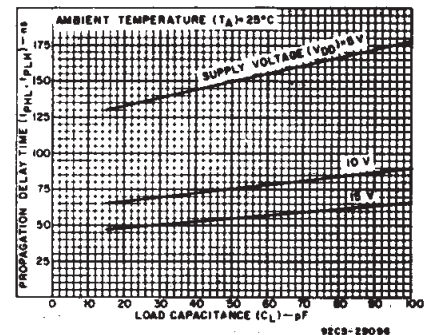


Fig. 8 - Typical propagation delay time as a function of load capacitance.

CD4068B Types

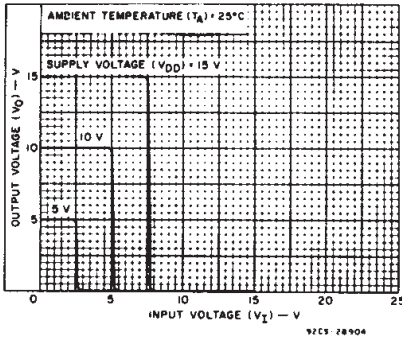


Fig. 9 - Typical voltage transfer characteristics (NAND output).

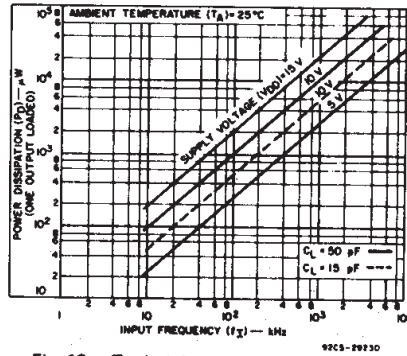


Fig. 10 - Typical dynamic power dissipation as a function of frequency.

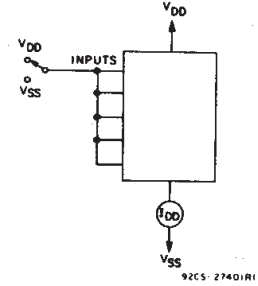


Fig. 11 - Quiescent-device-current test circuit.

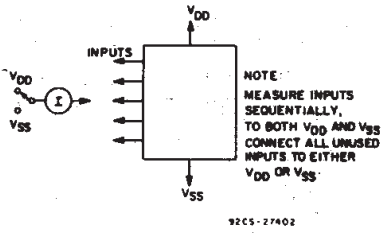


Fig. 12 - Input current test circuit.

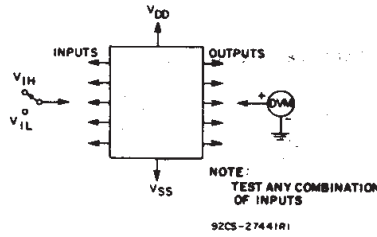


Fig. 13 - Input-voltage test circuit.

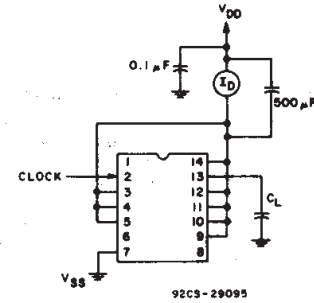
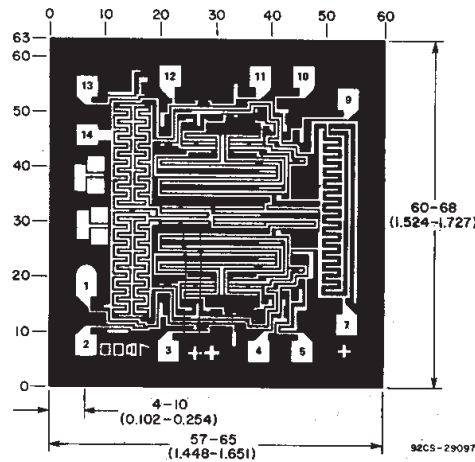


Fig. 14 - Dynamic power dissipation test circuit.



Dimensions and pad layout for CD4068BH.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10⁻³ inch).

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.